

Amendments to the Specification (other than claims):

Please replace paragraph [0068] with the following amended paragraph:

[0068] A further preferable condition is that the surface roughness of the wafer-carrying side be ~~[[5 μ m]]~~ 5 μ m in Ra. If the roughness is over ~~[[5 μ m]]~~ 5 μ m in Ra, grains loosened from the AlN due to friction between the ceramic susceptor and the wafer can grow numerous. Grain-loosened particles in that case become contaminants that have a negative effect on processes, such as film deposition and etching, on the wafer. Furthermore, then, a surface roughness of ~~[[1 μ m]]~~ 1 μ m or less in Ra is ideal.